Supporting Information

**Title:** Resistive switching characteristics of all-solution-based Ag/TiO₂/Mo-doped In₂O₃ devices for nonvolatile memory applications

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**Figure S1.** Schematic illustration of the anionic metal complexes coordinated with a water-soluble polymer in (a) Ti-PAS ink, (b) Mo-PAS ink, and (c) In-PAS ink.
Figure S2. (a) Transparency data and (b) optical image of all-solution-based Ag/TiO$_2$/Mo-doped In$_2$O$_3$ device on a glass substrate